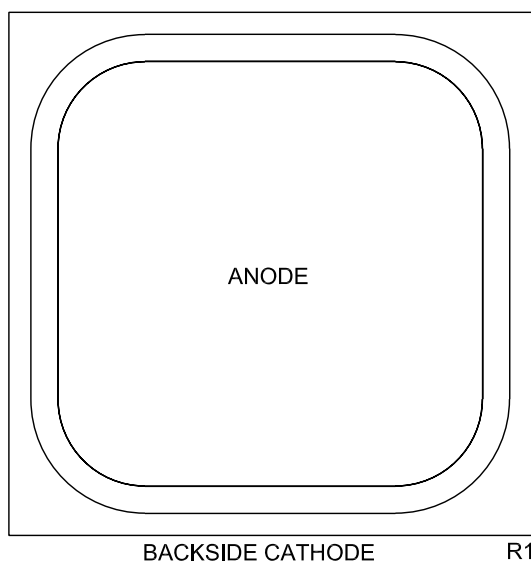


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	32 x 32 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	26 x 26 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 12,000Å

**GEOMETRY**



**GROSS DIE PER 4 INCH WAFER**

10,915

**PRINCIPAL DEVICE TYPES**

CMLSH1-40

1N5817

1N5818

1N5819

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